Advanced Semiconductor Business Inc.

ASF255

5-3000 MHz MMIC Amplifier

Features

- 22.4 dB Gain at 150 MHz
- 23 dBm P1dB at 150 MHz
- 42 dBm Output IP3 at 150 MHz
- 2.2 dB NF at 150 MHz
- MTTF > 100 Years
- Single Supply
- Minimal External Components

Description

The ASF255, a IF gain block amplifier MMIC, has a high linearity, high gain, and high efficiency over a wide range of frequency, being suitable for use in both receiver and transmitter of telecommunication systems up to 3 GHz. It has an active bias network for stable current over temperature and process variation. The amplifier is available in an SOT-89 package and passes through the stringent DC, RF, and reliability tests

RoHS-compliant GREEN Package

Package Style: SOT-89

Typical Performance

Parameters	Units	Typical					
Frequency	MHz	70	150	300	450	900	150
Gain	dB	22.4	22.4	22.2	21.9	21.0	22.1
S11	dB	-15.5	-18	-18	-16	-11	-18
S22	dB	-15.5	-20	-20	-20	-13	-20
Output IP3[1)]	dBm	39	42	42	40	38	40
Noise Figure	dB	2.2	2.2	2.3	2.3	2.3	2.2
Output P1dB	dBm	22.5	23.0	23.0	23.0	22.5	22.0
Current	mA	102	102	102	102	102	90
Device Voltage	V	5	5	5	5	5	4.5

1) OIP3 is measured with two tones at an output power of +8 dBm/tone separated by 1 MHz.

Product Specifications

Parameters	Units	Min	Typ	Max
Testing Frequency	MHz		150	
Gain	dB		22.4	
S11	dB		-18	
S22	dB		-20	
Output IP3	dBm		42	
Noise Figure	dB		2.2	
Output P1dB	dBm		23	
Current	mA		102	
Device Voltage	V		5	

Absolute Maximum Ratings

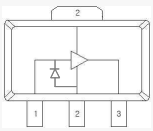
Parameters	Rating
Operating Case Temperature	-40 to +85°C
Storage Temperature	-40 to +150°C
Device Voltage	+6 V
Operating Junction Temperature	+150°C
Input RF Power (Continuous)	20 dBm

* Please find the max. input power data from http://www.asb.co.kr/pdf/Maximum_Input_Power_Analysis.pdf

Application Circuit

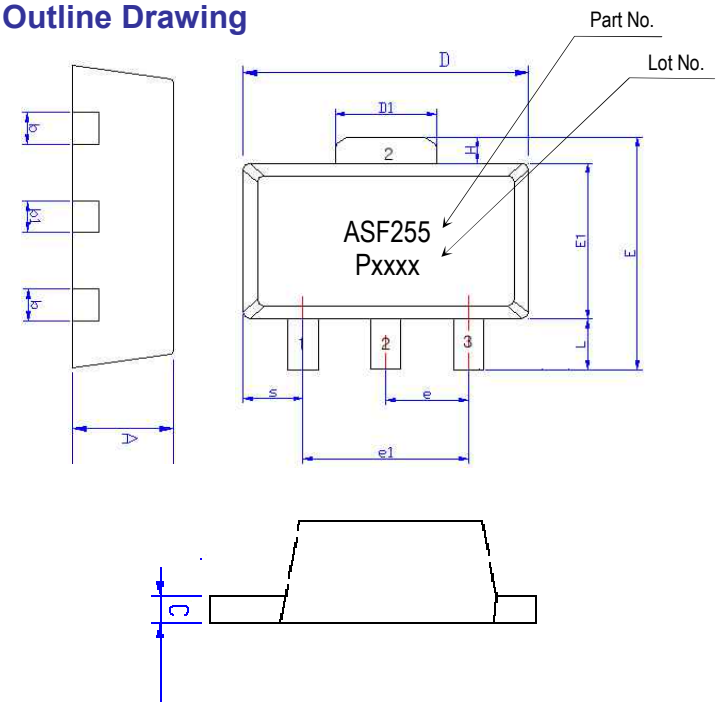
- 50 ~ 1000 MHz (5 V)
- 50 ~ 1000 MHz (4.5 V, 90 mA)
- 50 ~ 2150 MHz (5 V)
- 50 ~ 1000 MHz (6 V)

Pin Configuration



Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

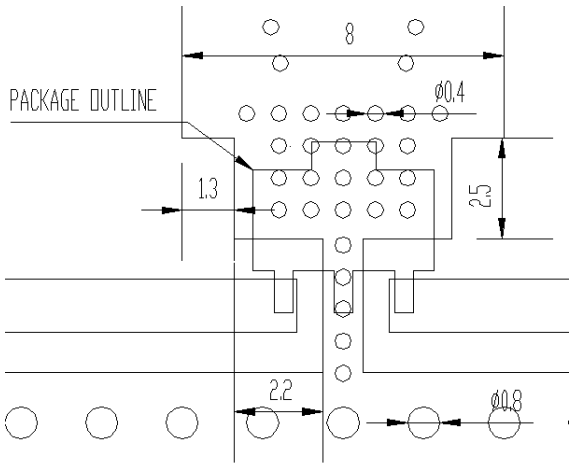
Outline Drawing



Symbols	Dimensions (In mm)		
	MIN	NOM	MAX
A	1.40	1.50	1.60
L	0.89	1.04	1.20
b	0.36	0.42	0.48
b1	0.41	0.47	0.53
C	0.38	0.40	0.43
D	4.40	4.50	4.60
D1	1.40	1.60	1.75
E	3.64	---	4.25
E1	2.40	2.50	2.60
e1	2.90	3.00	3.10
H	0.35	0.40	0.45
S	0.65	0.75	0.85
e	1.40	1.50	1.60

Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

Mounting Recommendation (in mm)



Note: 1. The number and size of ground via holes in a circuit board is critical for thermal and RF grounding considerations.
2. We recommend that the ground via holes be placed on the bottom of the lead pin 2 and exposed pad of the device for better RF and thermal performance, as shown in the drawing at the left side.

ESD Classification & Moisture Sensitivity Level

ESD Classification	
HBM	Class 2
	Voltage Level : 2000 V
MM	Class B
	Voltage Level: 200 V

CAUTION: ESD-sensitive device!

Moisture Sensitivity Level (MSL)
Level 3 at 260°C reflow

APPLICATION CIRCUIT

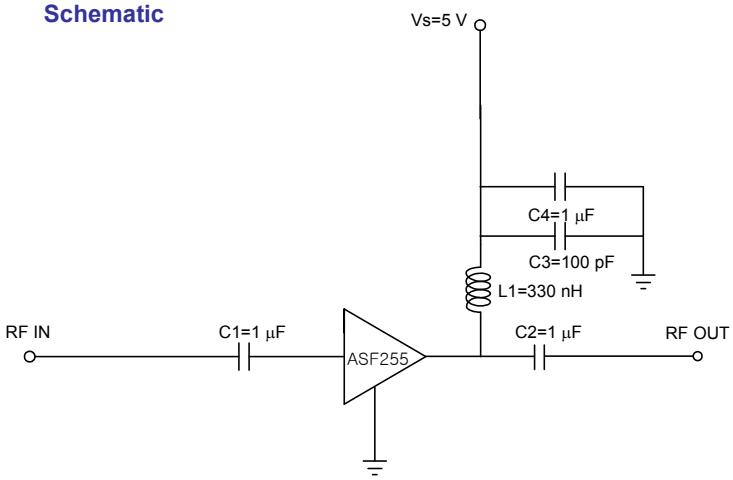
50 ~ 1000

+5 V

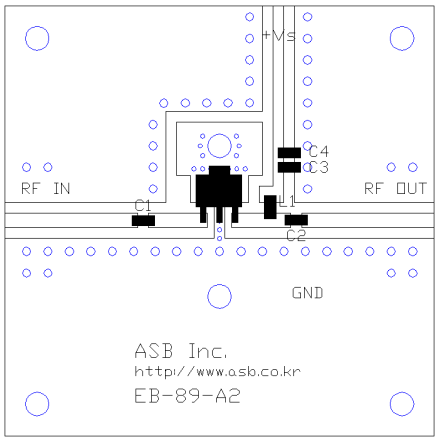
Frequency (MHz)	70	150	300	450	900
Magnitude S21 (dB)	22.4	22.4	22.2	21.9	21.0
Magnitude S11 (dB)	-15.5	-18	-18	-16	-11
Magnitude S22 (dB)	-15.5	-20	-20	-20	-13
Output P1dB (dBm)	22.5	23.0	23.0	23.0	22.5
Output IP3[1)] (dBm)	39	42	42	40	38
Noise Figure (dB)	2.2	2.2	2.3	2.3	2.3
Device Voltage (V)	5	5	5	5	5
Device Current (mA)	102	102	102	102	102

1) OIP3 is measured with two tones at an output power of +8 dBm/tone separated by 1 MHz.

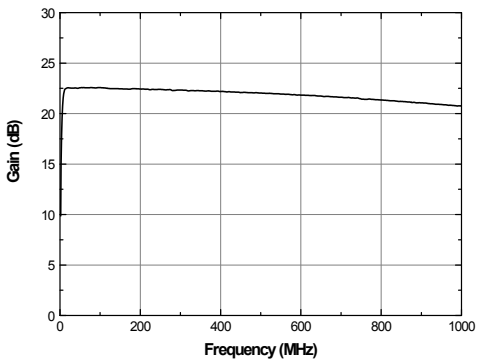
Schematic

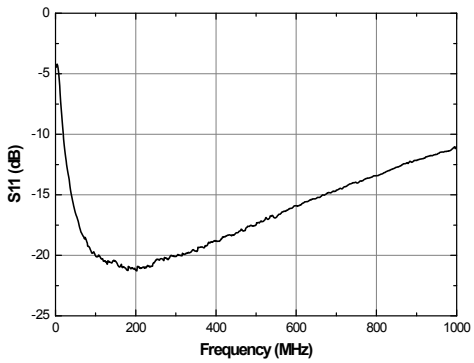


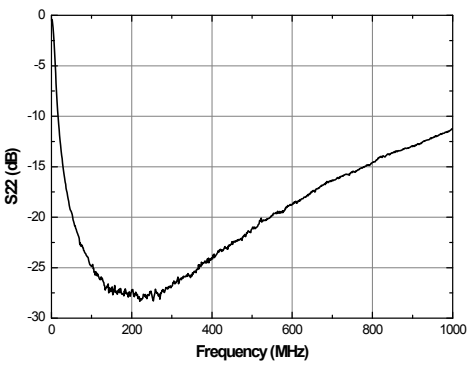
Board Layout (FR4, 40x40 mm^2, 0.8T)

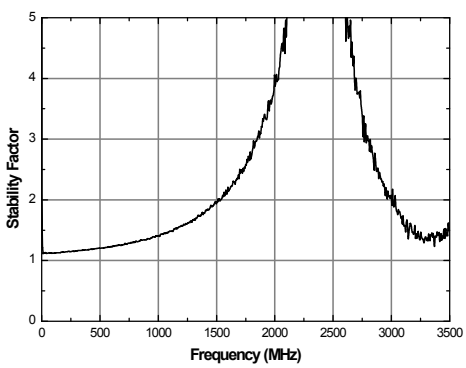


S-parameters & K-factor









APPLICATION CIRCUIT

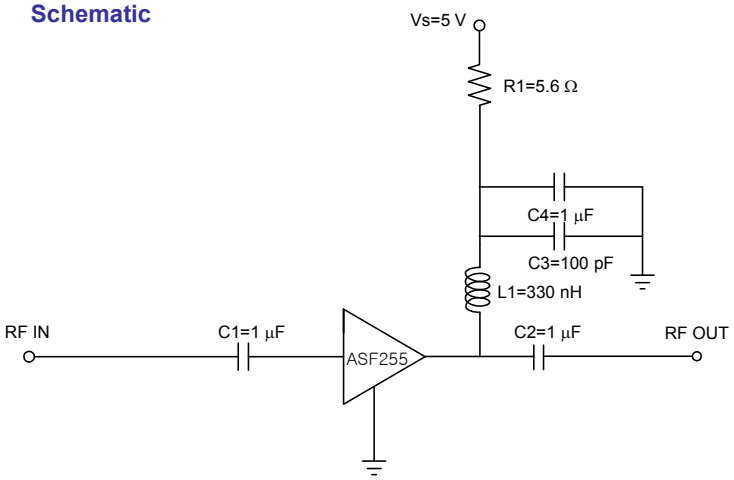
50 ~ 1000

+4.5 V, 90 mA

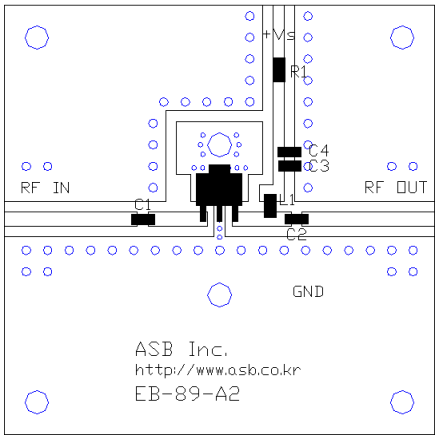
Frequency (MHz)	70	150	300	450	900
Magnitude S21 (dB)	22.2	22.1	21.9	21.7	20.8
Magnitude S11 (dB)	-15.5	-18	-18	-16	-11
Magnitude S22 (dB)	-15.5	-20	-20	-20	-13
Output P1dB (dBm)	21.5	22.0	22.0	22.0	21.0
Output IP3[1)] (dBm)	37.5	40.0	40.5	38.0	36.0
Noise Figure (dB)	2.2	2.2	2.3	2.3	2.3
Device Voltage (V)	4.5	4.5	4.5	4.5	4.5
Device Current (mA)	90	90	90	90	90

1) OIP3 is measured with two tones at an output power of +8 dBm/tone separated by 1 MHz.

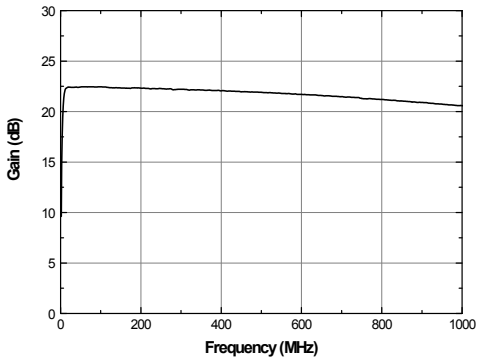
Schematic

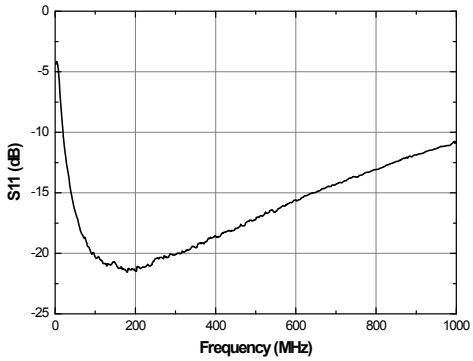


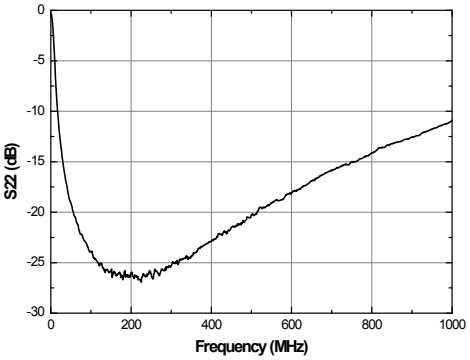
Board Layout (FR4, 40x40 mm^2, 0.8T)

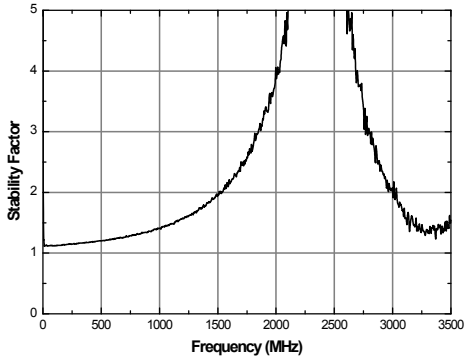


S-parameters & K-factor









APPLICATION CIRCUIT

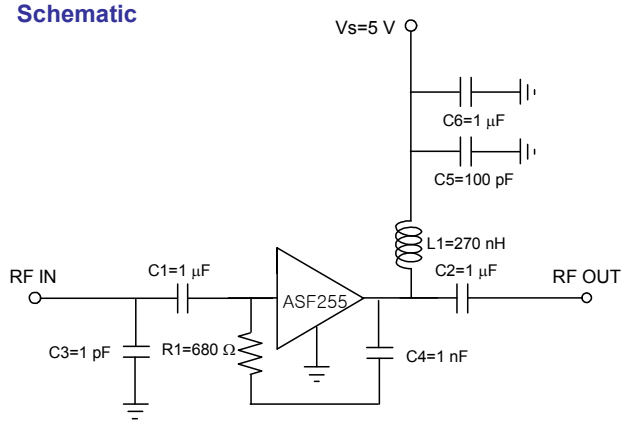
50 ~ 2150

+5 V

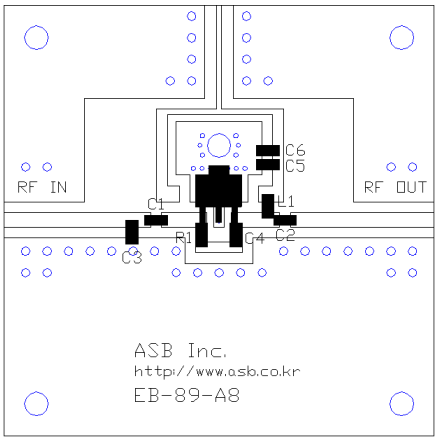
Frequency (MHz)	50	1000	2150
Magnitude S21 (dB)	18.2	18.4	18.1
Magnitude S11 (dB)	-8	-10	-14
Magnitude S22 (dB)	-8	-17	-7
Output P1dB (dBm)	21.5	21.5	20.0
Output IP3[1)] (dBm)	38	37	34
Noise Figure (dB)	2.5	2.6	3.0
Supply Voltage (V)	5	5	5
Current (mA)	102	102	102

1) OIP3 is measured with two tones at an output power of +5 dBm/tone separated by 1 MHz.

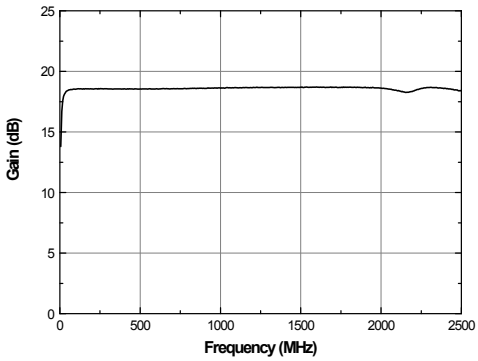
Schematic

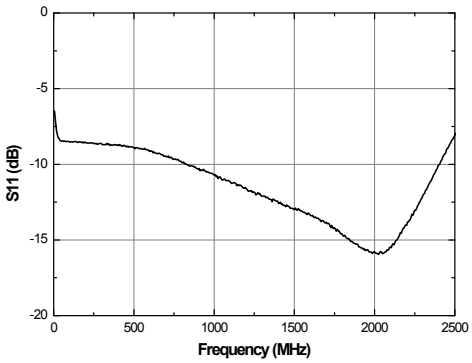


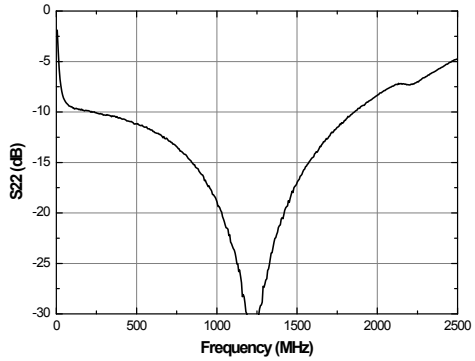
Board Layout (FR4, 40x40 mm^2, 0.8T)



S-parameters & K-factor







APPLICATION CIRCUIT

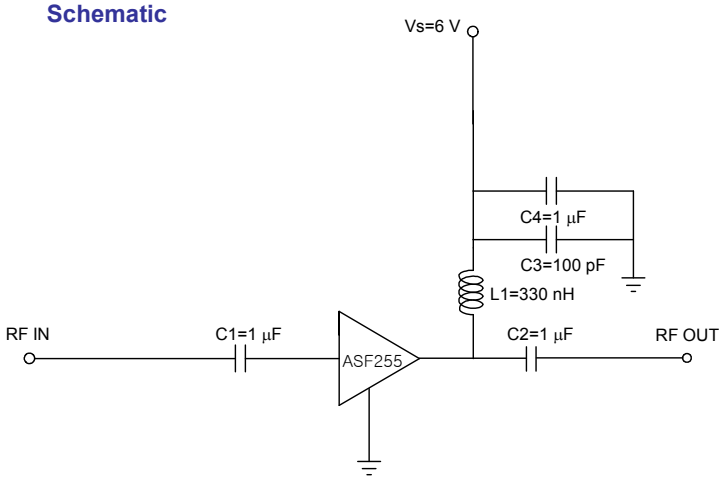
50 ~ 1000

+6 V

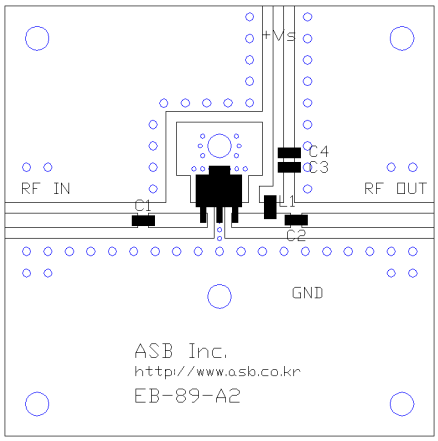
Frequency (MHz)	70	150	300	450	900
Magnitude S21 (dB)	22.9	22.8	22.7	22.4	21.4
Magnitude S11 (dB)	-15	-18	-18	-15	-10
Magnitude S22 (dB)	-15	-20	-20	-18	-11
Output P1dB (dBm)	24	24.5	24.5	24.5	24.5
Output IP3[1)] (dBm)	39.5	42.5	42	40.5	38.5
Noise Figure (dB)	2.4	2.4	2.5	2.5	2.5
Device Voltage (V)	6	6	6	6	6
Device Current (mA)	123	123	123	123	123

1) OIP3 is measured with two tones at an output power of +8 dBm/tone separated by 1 MHz.

Schematic



Board Layout (FR4, 40x40 mm^2, 0.8T)



S-parameters & K-factor